

PRODUCT CATALOG

P-CHANNEL JUNCTION FET

CHIP NUMBER

FP22.2



.013"
(0.330mm)

.016"
(0.406mm)

Die Size: 13 x 16 (mils)
0.330 x 0.406(mm)
4 x 6 (mils)
Pad Size: 0.102 x 0.152(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

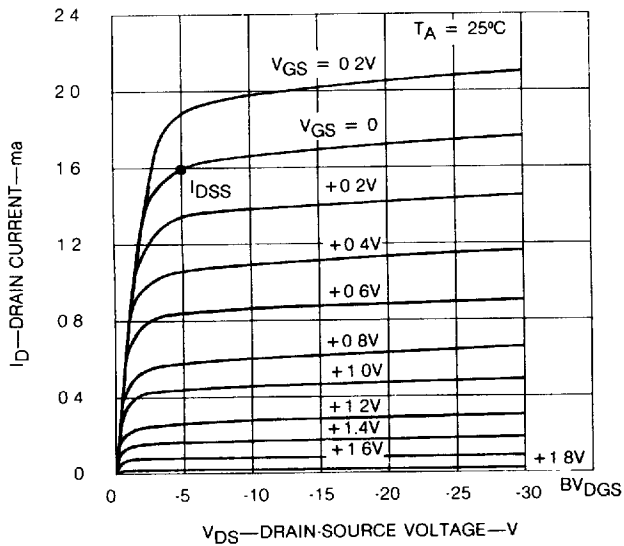
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV _{GSS}	40	55		V	V _{DS} = 0, I _G = 1μA
I _{DSS}	0.1		6	mA	V _{DS} = -15V, V _{GS} = 0
V _p	0.5		6	V	V _{DS} = -15V, I _D = 1nA
I _{GSS}		20	100	pA	V _{DS} = 0, V _{GS} = 30V
G _m	0.2	1	2	mS	V _{DS} = -15V, V _{GS} = 0, f = 1KHz
C _{iss}		4	5	pF	V _{DS} = -15, V _{GS} = 0, f = 1MHz
C _{rss}		0.9	1.5	pF	V _{DS} = -15V, V _{GS} = 0, f = 1MHz

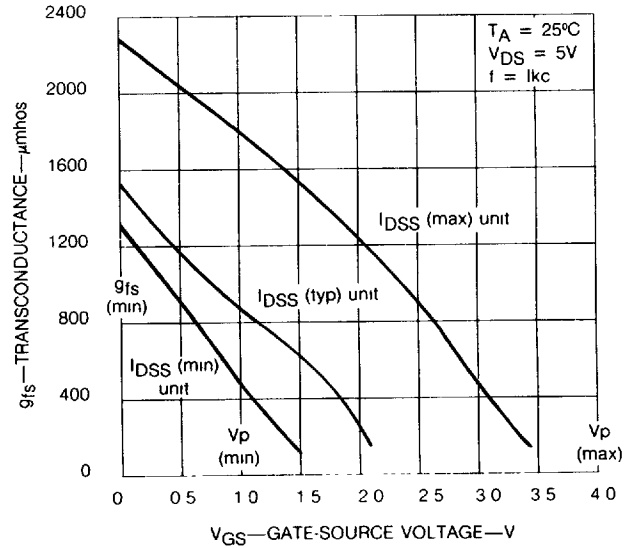
TYPICAL DEVICE TYPES: 2N2606 - 2N2608, 2N3376, 2N3378, 2N3695 - 2N3698

CHIP TYPE FP22..2

TYPICAL OUTPUT CHARACTERISTICS



TRANSCONDUCTANCE vs GATE-SOURCE VOLTAGE



TYPICAL TRANSFER CHARACTERISTICS WITH TEMPERATURE

